Modeling Internal Friction in Amorphous Oxides Using Two-Level Systems

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http://www.ligo.org/science/GW-Sources.php



http://10m-prototype.aei.uni-hannover.de/design-and-sensitivity



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Outline

- Describe Theory (W. A. Phillips Rep. Prog. Phys. 1987)
 - Introduce two-level systems (TLS)
 - Find the susceptibility
 - Calculate the internal friction
- Describe Model: Classical molecular dynamics (MD)
- Apply the model to Ta_2O_5 and SiO_2
- Conclusion

Two-Level System: The Basics

 Let's start by examining a two-level system (TLS). The Hamiltonian of the system is:

 $H = H_1 + (V - V_1) = H_2 + (V - V_2),$

where H_i is the Hamiltonian of isolated well *i*, and V_i is the potential of that well.

- Assume that the asymmetry is caused by coupling to an electric or mechanical field.
- In a localized representation, where φ_i and E_i are the harmonic oscillator wave function and energy in well *I*, the Hamiltonian is:

$$H = \begin{vmatrix} E_1 + \langle \varphi_1 | V - V_1 | \varphi_1 \rangle \\ \langle \varphi_2 | H | \varphi_1 \rangle \end{vmatrix}$$



Rashid Hamdan, J. Phys. Chem 2014.

 $<\varphi_1|H|\varphi_2>$ $E_2 + <\varphi_2|V - V_2|\varphi_2>$

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Two-Level System: The Basics

- •• We can diagonalize this Hamiltonian, and we obtain two states with $E = \pm \frac{E}{2} = \pm \frac{1}{2} \sqrt{\Delta^2 + \Delta_0^2}:$ $\psi_1 = \varphi_1 cos\theta + \varphi_2 sin\theta$ $\psi_2 = \varphi_1 sin\theta - \varphi_2 cos\theta$ Where tan(2\theta) = $\frac{\Delta_0}{\Delta}$. • Note that when $\Delta \gg \Delta_0$, $\psi_1 = \varphi_1$, and $\psi_2 = \varphi_2$.
- The other limit, when $\Delta \ll \Delta_0$, gives $\psi_1 = \frac{1}{\sqrt{2}}(\varphi_1 + \varphi_2)$ $\psi_2 = \frac{1}{\sqrt{2}}(\varphi_1 - \varphi_2)$

Two-Level System: Electric Susceptibility and Dipolar Relaxation

• Using the relaxation time approximation for the population difference, and assuming a wave of the form $\xi(t) = \xi_0 e^{-i\omega t}$, we get that the dielectric susceptibility is

$$\chi(\omega) = \frac{\chi(0)}{1 - i\omega\tau} = \frac{\bar{\alpha}}{1 - i\omega\tau}$$

 To find the energy lost to this system of dipoles, we need to find the imaginary part of the susceptibility:

$$\chi^{\prime\prime}(\omega) = \frac{\omega\tau}{1+\omega^2\tau^2}\bar{\alpha} = \frac{\omega\tau}{1+\omega^2\tau^2}\frac{p_0^2}{3kT}\frac{\Delta^2}{E^2}sech^2(\frac{E}{2kT})$$

Two-Level System: Mechanical Loss

• This leads to the total internal friction for the system:

$$Q^{-1} = \frac{1}{(3kT)\varepsilon} \iint d\Delta dV \frac{\omega\tau}{1+\omega^2\tau^2} \gamma^2 sech^2 \left(\frac{\Delta}{2kT}\right) N(\Delta, V)$$

where

- $N(\Delta, V)$ is a number density of TLS's
- $\boldsymbol{\gamma}$ is the mechanical dipole
- $\boldsymbol{\tau}$ is the relaxation time
- $\boldsymbol{\omega}$ is the angular frequency of the wave
- ε is the Young's modulus for the system

Classical MD Basics

- Classical description of forces:
 - Built on F=ma
 - Interatomic potentials are modeled to fit experimental data (Density, elastic moduli, radial distribution functions, etc.)
 - Potentials were developed by Jonathan Trinastic.

$$V_{1-2}(r) = Ae^{-Br} - \frac{C}{r^6} + \frac{kq_1q_2}{r^2}$$



https://en.wikipedia.org/wiki/Buckingham_potential

The TLS model in MD



- We do this method thousands of times, to get N(Δ, V).
- We calculate the average relaxation time and average coupling constant from a subset of these TLS's

Rashid Hamdan, unpublished.

Model Inputs: TLS Distribution



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Mechanical Loss: Approximations

- Asymmetry Cut-off
 - Previously, a 0.1 eV asymmetry cut-off was used to better match



What our model contributes



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Temperature (K)



Q⁻¹ 10⁻³

Conclusion

- The acoustic loss in amorphous solids is a consequence of applying a mechanical field to systems of dipoles, and can be derived from a model Hamiltonian where we assume two-level systems where symmetry is broken by an applied field.
- Using classical molecular dynamics to provide inputs for the TLS model gives good agreement with the low temperature peak. Using the 2-D distribution, more detailed features can be seen at higher temperature.
 - For SiO₂ this shows a second peak at 150K which matches experiment.
 - For Ta_2O_5 , it does not lead to a better description but better statistics may be required.
- This allows us to
 - Understand the atomic transitions that cause internal friction
 - Predict internal friction under different doping
 - Determine what causes higher temperature peaks

Model Inputs: Elastic Moduli and Coupling

- •• Young's modulus
 - $\sigma_i = c_{ij}\varepsilon_i$
 - Strain the system to determine what the elastic moduli are. To compare to mechanical loss experiments, we are interested in longitudinal modes, so we need the Young's modulus.
 - Coupling Constant
 - $\gamma_j = 1/2 \frac{\partial \Delta}{\partial u_j}$
 - The asymmetry changes as unit cell is strained, which is the coupling to mechanical field.



Model Inputs: Relaxation Time

• The relaxation time is calculated using the Arrhenius law:

$$\tau = \tau_0 e^{\frac{V}{kT}} \operatorname{sech}(\frac{\Delta}{2kT})$$

and is averaged over all TLS's found.

• In the Arrhenius law, the shape of the well changes the attempt frequency, which is inversely related to τ_0 . This value is calculated for each TLS by

$$\tau_0^{-1} = \frac{\prod_{i=1}^{3N} v_i^0}{\prod_{i=1}^{3N} v_i^s} e^{S/k}$$

where v_i^o are the vibrational frequencies at the minimum, v_i^s are the vibrational frequencies at the saddle point. The exponential represents the entropy term, as a single well may be a part of many different TLS's.